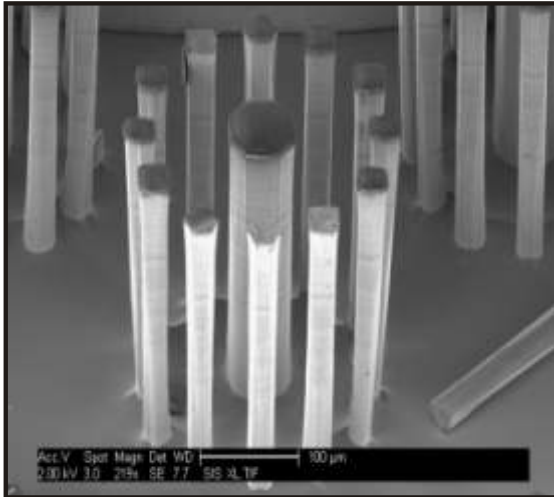
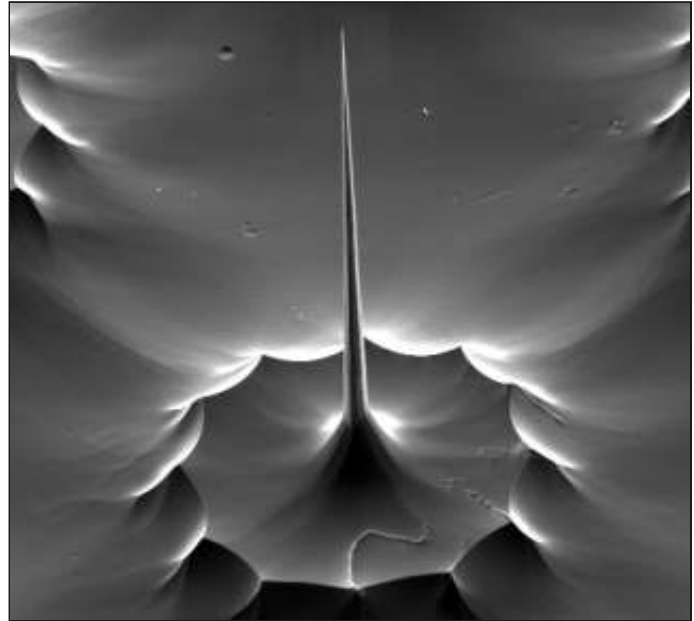


# Plasmalab Data

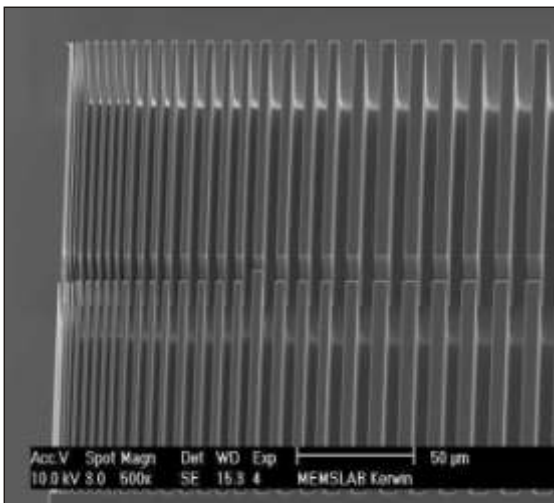
## Deep Si Etching for MEMS and Si tips (Bosch Process)



250 µm deep anisotropic etch



Si tips for field emission arrays or AFM



50 µm deep etch at high aspect ratios

- Plasmalab System 100*
- Plasmalab System 133*
- Plasmalab 80 Plus*



Technology:  
Reactive Ion Etching  
Inductive Coupled Plasma Source  
room temperature “Bosch” process  
He backside cooling

Results:  
Rate : 1 - 5 µm/min  
Rates up to 10 µm/ min are possible  
with the ICP 380 source.  
anisotropic etch  
aspect ratio up to 30 : 1  
controllable wall profile

